AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 1, line 18, with the following amended paragraph:

As the integration density of semiconductor devices, such as DRAMs, increases, manufacturing gate oxide films or capacitors using a silicon oxide (SiO_2) film becomes more complicated. Thus, more ~~attentions~~ attention is given and studies are done for materials having a dielectric constant that is higher than that of the silicon oxide film.

Please replace the paragraph beginning on page 1, line 28, with the following amended paragraph:

In recent years, attempts [[are]] have been made to form capacitors or gate oxide films of DRAMs using high k-dielectric materials, such as HfO_2, ZrO_2, and $SrTiO_3$. However, in a metal/insulator/silicon (MIS) structure in which a lower electrode is formed of silicon (Si), since the high k-dielectric materials generally have low band offset, [[the]] leakage current increases. For this reason, it is actually difficult to apply these high k-dielectric materials to the MIS structure.